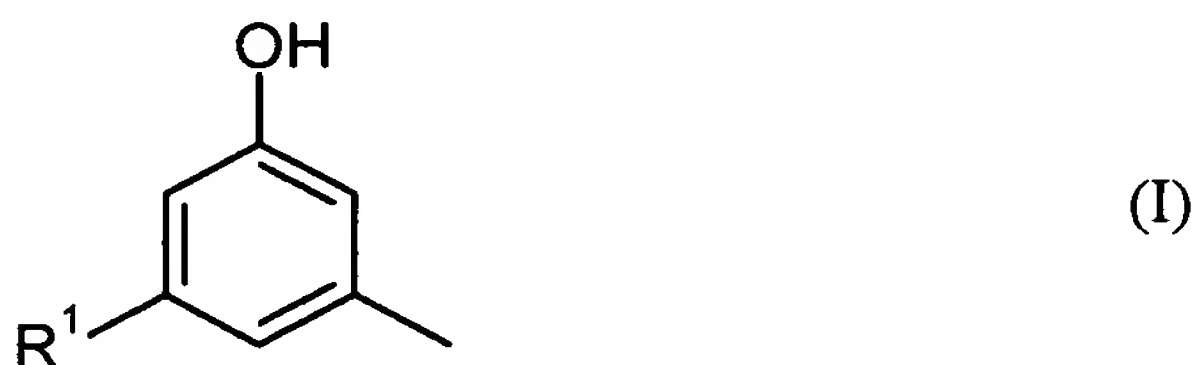


**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A Mannich base ~~characterized in that it is prepared~~ using at least one phenolic compound of the formula (I)



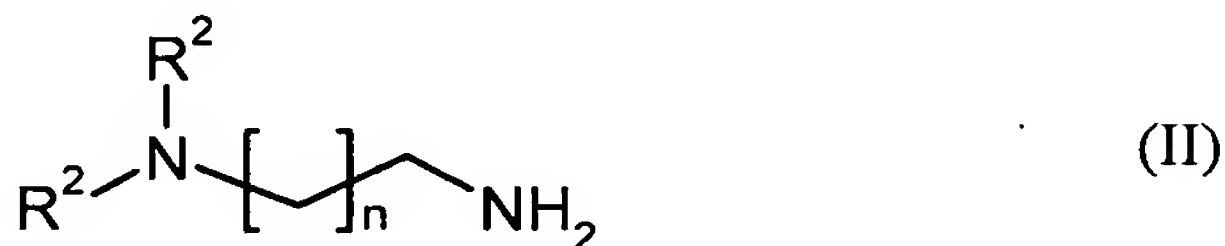
with  $R^1 = \text{H or CH}_3$

~~and also a formaldehyde and at least one polyamine.~~ polyamine, wherein the Mannich base is prepared by:

reacting the phenolic compound with the formaldehyde in the presence of a tertiary amine; and

reacting a resulting product with the at least one polyamine.

2. (Canceled)
3. (Currently Amended) The Mannich base as claimed in ~~claim 2,~~ claim 1, ~~characterized in that~~ wherein the tertiary amine has the formula (II)



with  $R^2 = \text{C}_1\text{-C}_6$  alkyl and  $n = 1, 2, \text{ or } 3$ .

4. (Currently Amended) The Mannich base as claimed in ~~claim 2,~~ claim 1, ~~characterized in that in the first stage~~ wherein the formaldehyde is added to a mixture of the phenolic compound of formula (I) and the tertiary amine.

5. (Currently Amended) The Mannich base as claimed in claim 1, ~~characterized in that in formula (I)  $R^1 = H$ , wherein  $R^1 = H$  in formula (I).~~

6. (Currently Amended) The Mannich base as claimed in claim 3, ~~characterized in that in formula (II)  $R^2 = CH_3$ , wherein  $R^2 = CH_3$  in formula (II).~~

7. (Currently Amended) The Mannich base as claimed in claim 3, ~~characterized in that in formula (II)  $n = 2$ , wherein  $n = 2$  in formula (II).~~

8. (Currently Amended) The Mannich base as claimed in claim 1, ~~characterized in that wherein the viscosity at 25°C is less than 1000 mPas, mPas, and in particular is in the range between 200 and 700 mPas.~~

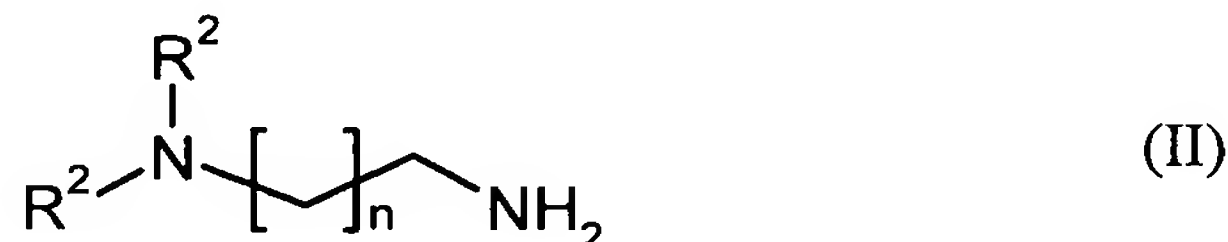
9. (Currently Amended) A process for preparing a Mannich base, ~~characterized in that in a first stage comprising:~~

reacting at least one phenolic compound is reacted with formaldehyde in the presence of a tertiary amine and in a subsequent stage reaction takes place amine; and

reacting a resulting product with at least one polyamine.

10. (Currently Amended) The process for preparing a Mannich base as claimed in claim 9, ~~characterized in that in the first stage wherein the formaldehyde is added to a mixture of the phenolic compound and the tertiary amine.~~

11. (Currently Amended) A process for preparing a Mannich base as claimed in claim 9, ~~characterized in that wherein the tertiary amine has the formula (II)~~



with  $R^2 = C_1-C_6$  alkyl and  $n = 1, 2, \text{ or } 3$ .

12. (Currently Amended) The process for preparing a Mannich base as claimed in claim 11, ~~characterized in that in formula (II)  $R^2 = CH_3$ , wherein  $R^2 = CH_3$  in formula (II).~~

13. (Currently Amended) The process for preparing a Mannich base as claimed in claim 11, ~~characterized in that in formula (II)  $n = 2$~~ , wherein  $n = 2$  in formula (II).

14. (Currently Amended) The process for preparing a Mannich base as claimed in claim 9, ~~characterized in that~~ wherein the phenolic compound is a phenolic compound of the formula (I)



with  $R^1 = H$  or  $CH_3$ .

15. (Currently Amended) The process for preparing a Mannich base as claimed in claim 14, ~~characterized in that in formula (I)  $R^1 = H$~~ , wherein  $R^1 = H$  in formula (I).

16. (Currently Amended) A hardener component for two-component epoxy systems or polyurethane systems, ~~characterized in that this~~ wherein the hardener component comprises a Mannich base as claimed in claim 1.

17. (Canceled)

18. (Previously Presented) An epoxy system or polyurethane system comprising at least one Mannich base as claimed in claim 1.

19. (Previously Presented) An epoxy system or polyurethane system comprising at least one Mannich base and obtained by a process as claimed in claim 9.

20. (Previously Presented) A cured product obtained from an epoxy system or polyurethane system as claimed in claim 19.

21. (New) The Mannich base as claimed in claim 1, wherein the viscosity at  $25^\circ\text{C}$  is in the range between 200 and 700 mPas.